

SMP600G-EK

MECHANICAL DATA

Dimensions in mm.

WINDOW Ø 8.1 ± 0.1 SENSITIVE SURFACE Ø 0.45 LEAD 5.08 ± 0.2

TO-39 Package

Pin 1 – Anode

Pin 2 - Cathode & Case

P.I.N. PHOTODIODE

FEATURES

- EXCELLENT LINEARITY
- LOW NOISE
- WIDEST SPECTRAL RESPONSE
- ENHANCED UV SENSITIVITY
- INTEGRAL OPTICAL FILTER OPTION note 1
- TO39 HERMETIC METAL CAN PACKAGE
- EMI SCREENING MESH AVAILABLE

Note 1 Contact Semelab Plc for filter options

DESCRIPTION

The SMP600G-EK is a Silicon P.I.N. photodiode incorporated in a hermetic metal can package. The package window has greater ultra-violet light transmission, thus extending the useful spectral range of the device. The electrical terminations are via two leads of diameter 0.018" on pitch of 0.2". The cathode of the photodiode is electrically connected to the package.

The larger photodiode active area provides greater sensitivity than the SMP550 range of devices, with a slight reduction in speed. Inherent in the device geometry is a reduction in the receiving angle. The photodiode structure has been optimised for high sensitivity, light measurement applications across the infra-red to ultra-violet spectrum. Inclusion of a suitable optical filter into the package can produce a device that responds only to ultra-violet light. The metal can and optional screening mesh ensure a rugged device with a high degree of immunity to radiated electrical interference.

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25$ °C unless otherwise stated)

Operati	ng temperature range	-40°C to +70°C	
Storage	temperature range	-45°C to +80°C	
Temper	ature coefficient of responsively	0.35% per °C	
Temper	ature coefficient of dark current	x2 per 8°C rise	
Reverse	e breakdown voltage	60V	
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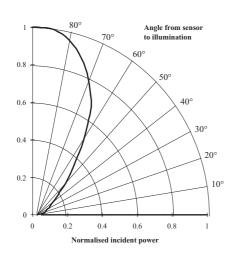


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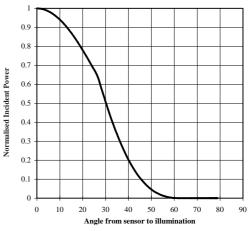
CHARACTERISTICS (T_{amb}=25°C unless otherwise stated)

Characteristic	Test Conditions.		Min.	Тур.	Max.	Units	
Responsively	λ at 900nm		0.45	0.55		A/W	
Active Area				15		mm²	
Dark Current	E = 0 Dark	1V Reverse		2	6	nA	
Dark Guilent	E = 0 Dark	10V Reverse					
Breakdown Voltage	E = 0 Dark	10µA Reverse	60	80		V	
Capacitance	E = 0 Dark	0V Reverse		90		pF	
Capacitance	E = 0 Dark	20V Reverse		25] Pi	
Rise Time	30V Reverse		12			ns	
IXISE TITLE	50Ω			12		115	
NEP	900nm			20x10 ⁻¹⁴	0.45	W/√Hz	

Directional characteristics



Directional Characteristics



Spectral Response

